

# **BUK763R8-80E**

# N-channel TrenchMOS standard level FET

28 July 2016

Product data sheet

## 1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> rating of greater than 1 V at 175 °C

# 3. Applications

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- · Ultra high performance power switching

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	80	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	120	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	349	W	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		-	3.1	3.8	mΩ	
Dynamic characteristics								
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 64 \text{ V};$ Fig. 13; Fig. 14		-	51	-	nC	

[1] Continuous current is limited by package.



# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G—VIII
mb	D	mounting base; connected to drain	1 3	mbb076 S
			D2PAK (SOT404)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK763R8-80E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK763R8-80E	BUK763R8-80E

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	80	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$		-	80	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	349	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	120	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	120	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 3		-	778	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
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Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	778	Α
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 120 A; $V_{sup}$ ≤ 80 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2][3]	-	488	mJ

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

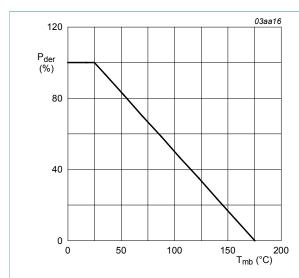


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

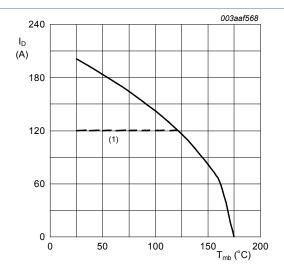


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10 V$ 

(1) Capped at 120 A due to package.

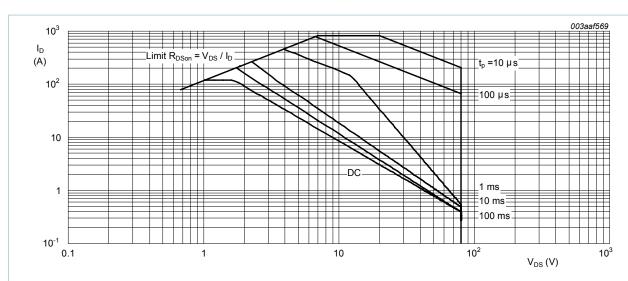
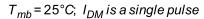


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



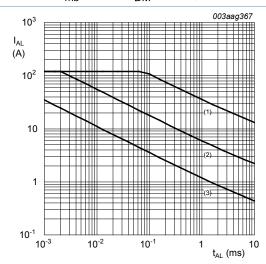


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time.

(1) 
$$T_{j(init)} = 25$$
°C; (2)  $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

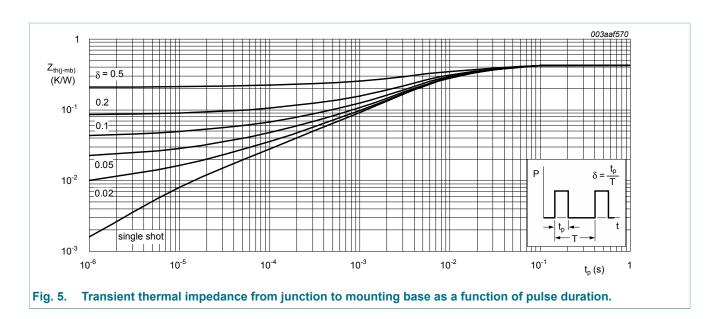
### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	0.43	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

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## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Static characteristics									
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		80	-	-	V		
	breakdown voltage	$I_D = 250 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$		72	-	-	V		
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10		2.4	3	4	V		
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9		1	-	-	V		
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9		-	-	4.5	V		
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	0.15	1	μΑ		
		V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C		-	-	500	μΑ		
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	2	100	nA		
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	2	100	nA		
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 11		-	3.1	3.8	mΩ		
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11		-	-	9.2	mΩ		
Dynamic characteristics									
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 10 V;		-	169	-	nC		
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14		-	37	-	nC		
$Q_{GD}$	gate-drain charge			-	51	-	nC		

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	9020	12030	pF
C <sub>oss</sub>	output capacitance			-	840	1010	pF
C <sub>rss</sub>	reverse transfer capacitance			-	470	645	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 60 V; $R_L$ = 2.4 $\Omega$ ; $V_{GS}$ = 10 V;		-	38	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$		-	48	-	ns
$t_{d(off)}$	turn-off delay time	_		-	129	-	ns
t <sub>f</sub>	fall time			-	65	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of mounting base to centre of die		-	2.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad; $T_j$ = 25 °C		-	7.5	-	nΗ
Source-dra	in diode		l				
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	0.77	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	58	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V		-	121	-	nC

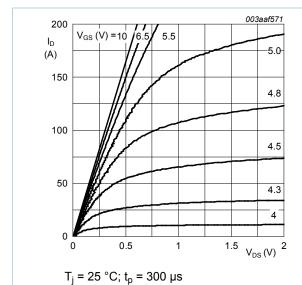


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

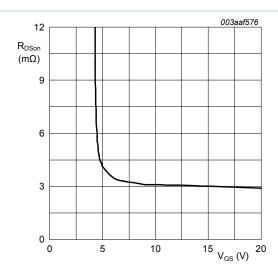


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C; I_D = 25A$$

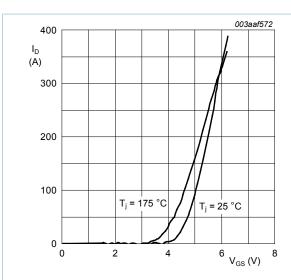


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



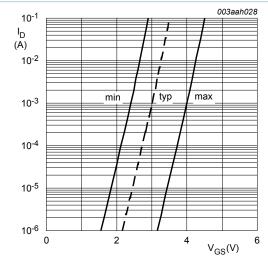


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

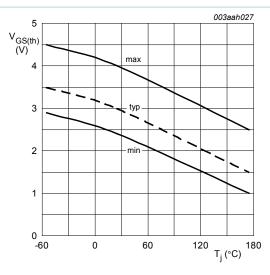
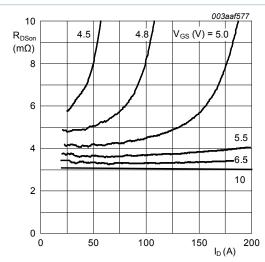


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA;  $V_{DS}$  =  $V_{GS}$ 



 $T_i$  = 25 °C;  $t_p$  = 300  $\mu$ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

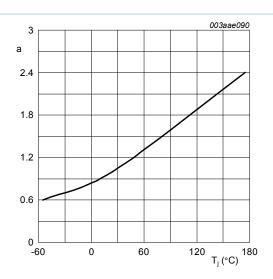


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

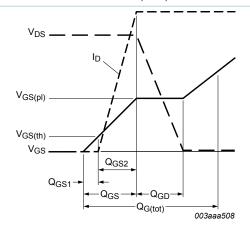
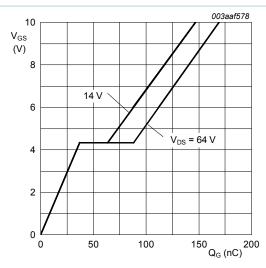
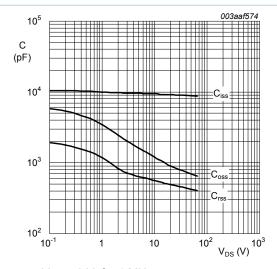


Fig. 14. Gate charge waveform definitions



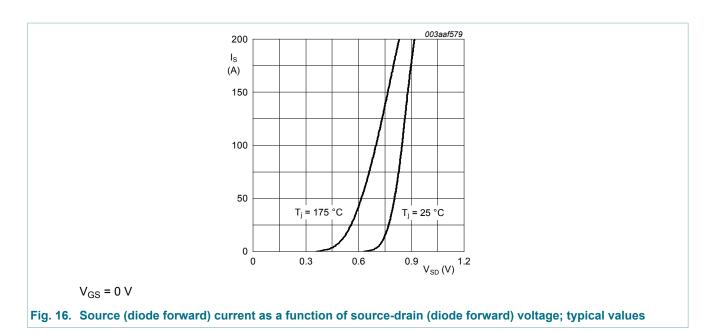
 $T_i = 25 \,^{\circ}\text{C}; I_D = 25 \,^{\circ}\text{A}$ 

Fig. 13. Gate-source voltage as a function of gate charge; typical values

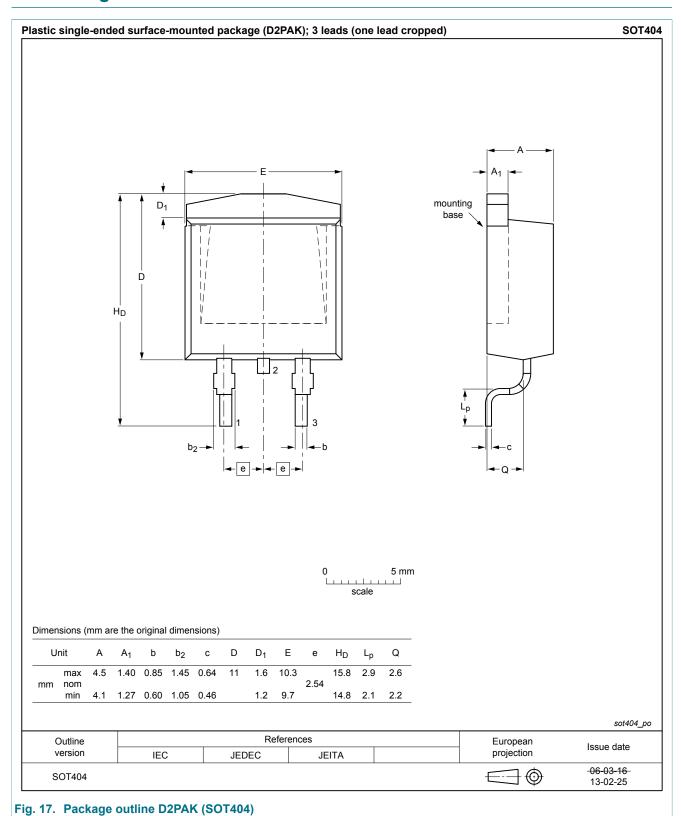


 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



# 11. Package outline



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